

## SEMITOP® 3

# 3-phase bridge rectifier + brake chopper

#### SK 95 DGL 126

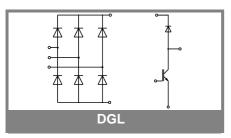
**Target Data** 

#### **Features**

- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench IGBT technology
- CAL Technology FWD

### **Typical Applications**

Rectifier

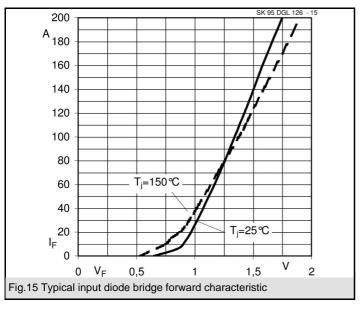


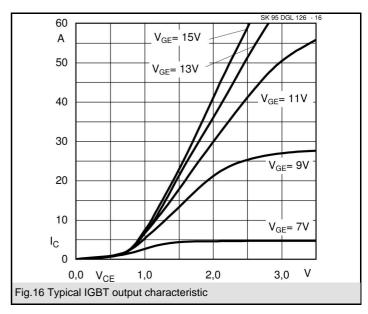
<b>Absolute Maximum Ratings</b> T <sub>s</sub> = 25°C, unless otherwise specified								
Symbol	Conditions	Values	Units					
IGBT - Chopper								
$V_{CES}$		1200	V					
I <sub>C</sub>	T <sub>s</sub> = 25 (80) °C	40 (32)	Α					
I <sub>CRM</sub>	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	70	Α					
$V_{GES}$		±20	V					
T <sub>j</sub>		-40 <b>+</b> 150	°C					
Diode - Chopper								
I <sub>F</sub>	T <sub>s</sub> = 25 (80) °C	45 (35)	Α					
I <sub>FRM</sub>	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	100	Α					
T <sub>j</sub>	·	-40 <b>+</b> 150	°C					
Rectifier								
$V_{RRM}$		1600	V					
I <sub>D</sub>	T <sub>s</sub> = 80 °C	96	Α					
I <sub>FSM</sub> / I <sub>TSM</sub>	$t_p = 10 \text{ ms}$ , sin 180 °, $T_i = 25 \text{ °C}$	700	Α					
I <sup>2</sup> t	t <sub>p</sub> = 10 ms , sin 180 ° ,T <sub>i</sub> = 25 °C	2450	A²s					
T <sub>j</sub>	,	-40 <b>+</b> 150	°C					
T <sub>sol</sub>	Terminals, 10s	260	°C					
T <sub>stg</sub>		-40 <b>+</b> 125	°C					
V <sub>isol</sub>	AC, 1 min. / 1s	2500 / 3000	V					

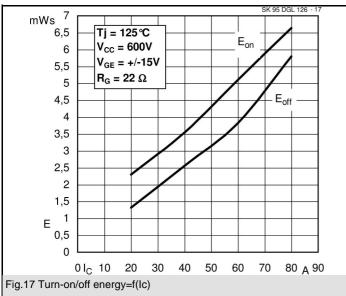
Characteristics		T <sub>s</sub> = 25°C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Chopper								
V <sub>CEsat</sub> V <sub>GE(th)</sub> V <sub>CE(TO)</sub> r <sub>T</sub> C <sub>ies</sub>	$I_C = 35 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ $V_{GE} = V_{CE}, I_C = 1,5 \text{ mA}$ $T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ $V_{CE} = 25 V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	5	1,7 (2) 5,8 1 (0,9) 20 (31) 2,4	2,1 6,5 1,2 26	V V V mΩ nF			
C <sub>oes</sub> C <sub>res</sub> R <sub>th(j-s)</sub>	$V_{CE} = 25 V_{GE} = 0 V$ , f = 1 MHz $V_{CE} = 25 V_{GE} = 0 V$ , f = 1 MHz per IGBT		0,5 0,4	1,05	nF nF K/W			
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub>	under following conditions $\begin{aligned} &V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V} \\ &I_{C} = 30 \text{ A}, T_{j} = 125 \text{ °C} \\ &R_{Gon} = R_{Goff} = 22 \Omega \\ &\text{inductive load} \end{aligned}$		85 30 430 90 4,6 4,3		ns ns ns ns mJ mJ			
$ \begin{aligned}                                   $	In opper $  I_F = 45 \text{ A}, T_j = 25 (125) \text{ °C} $ $  T_j = \text{ °C} (125) \text{ °C} $ $  T_j = $		1,5 (1,5) (0,92) (13,4) 30 10	1,77 (1,77)	V V mΩ K/W A μC mJ			
Diode rectifier								
$V_{F} \\ V_{(TO)} \\ r_{T} \\ R_{th(j-s)}$	$I_F = 35 \text{ A}, T_j = 25 \text{ °C}$ $T_j = 150 \text{ °C}$ $T_j = 150 \text{ °C}$ per diode			1,2 0,8 11 1,2	V V mΩ K/W			
Temperatur sensor								
R <sub>ts</sub>	%, T <sub>r</sub> = () °C		()		Ω			
Mechanical data								
w M <sub>s</sub>	Mounting torque		30	2,5	g Nm			

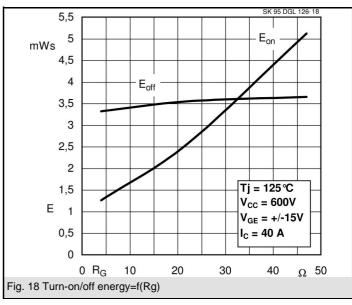
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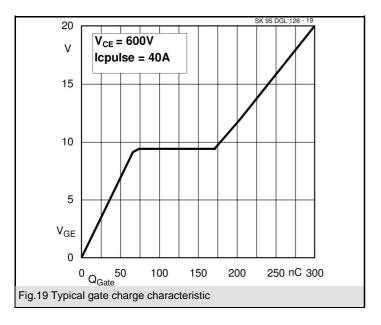
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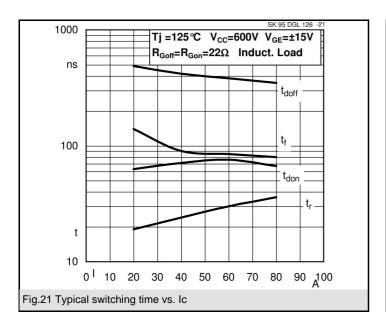


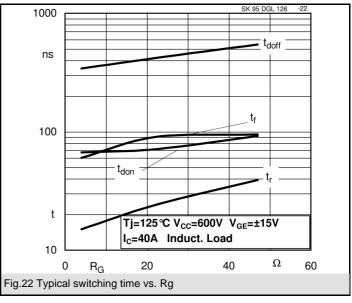




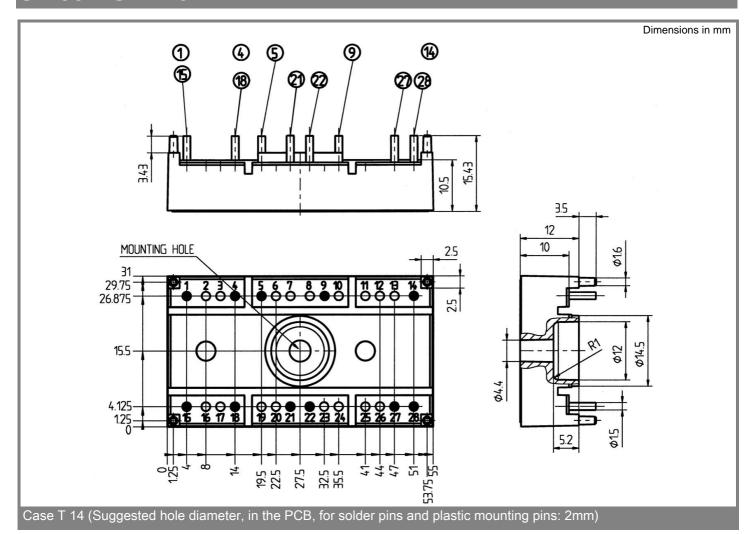


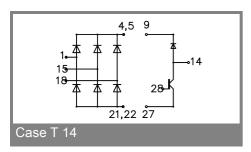
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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